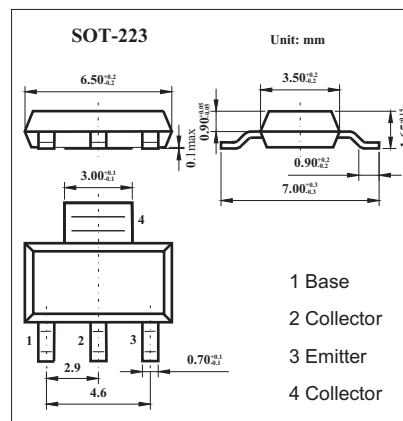


PNP Silicon Planar Medium Power High Transistor FZT1151A

Features

Low saturation Voltage

High Gain



Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-45	V
Collector-emitter voltage	V_{CE0}	-40	V
Emitter-base voltage	V_{EB0}	-5	V
Continuous Collector Current	I_C	-3	A
power dissipation	P_C	2.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$	-45			V
Collector to emitter breakdown voltage	V_{CE0}	$I_C = -10\text{mA}$	-40			V
Emitter to base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$	-5.0			V
Collector cut-off current	I_{CBO}	$V_{CB} = -36\text{V}, I_E = 0$			-100	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-100	nA
DC current gain	h_{FE}	$I_C = -10\text{mA}; V_{CE} = -2\text{V}$	270	450		
		$I_C = -500\text{mA}; V_{CE} = -2\text{V}$	250		800	
		$I_C = -2\text{A}; V_{CE} = -2\text{V}$	180	300		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.8\text{A}; I_B = -70\text{mA}$			-0.26	V
		$I_C = -3\text{A}; I_B = -250\text{mA}$			-0.3	V
Output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$		40		pF
Transition frequency	f_T	$I_C = -50\text{mA}; V_{CE} = -10\text{V}; f = 50\text{MHz}$		145		MHz

Marking

Marking	1151A
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